

NPN Silicon Planar High Voltage Transistor

FEATURES

- High BV_{CEO}, BV_{CBO}
- High current gain
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-Free according to IEC 61249-2-21

Δ	PF	L	IC	Δ٦	ΓIO	N

- Lighting
- Switch mode power supply

KEY PERFORMANCE PARAMETERS				
PA	RAMETER	VALUE	UNIT	
BV_CEO		400	V	
BV _{CBO}		600	V	
I _C		300	mA	
V _{CE(SAT)}	I _C =50mA, I _B =5mA	0.5	٧	

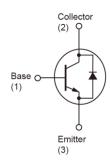












Notes: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Collector-Base Voltage		V_{CBO}	600	V
Collector-Emitter Voltage		V_{CES}	600	V
Collector-Emitter Voltage @ V _{BE} =0V		V _{CES}	400	V
Emitter-Base Voltage		V_{EBO}	7	V
O-Hanton Orangat	DC	I _C	0.3	Α
Collector Current	Pulse		1	А
Power Total Dissipation @ T _A =25°C		P _{DTOT}	1	W
Maximum Operating Junction Temperature		T_J	+150	°C
Storage Temperature Range		T _{STG}	-55 to +150	°C

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction to Ambient Thermal Resistance	R _{OJA}	91	°C/W		
Junction to Case Thermal Resistance	R _{eJC}	25	°C/W		



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 1)						
Collector-Base voltage	I _C =50μA	BV _{CBO}	600			V
Collector-Emitter Saturation Voltage	$I_C = 100 \mu A, V_{BE} = 0$	BV _{CES}	600			V
Collector-Emitter breakdown voltage	I _C =1mA	BV _{CEO}	400			V
Emitter-Base breakdown voltage	I _E =50μA	BV _{EBO}	7			V
Emitter cut-off current	V _{EB} =7V	I _{EBO}			1.5	μΑ
Collector cut-off current	V _{CB} =600V	I _{CBO}			0.5	μΑ
Collector-Emitter Cutoff Current	V _{CE} =400V	I _{CEO}			1	μΑ
Collector-Emitter saturation voltage	$I_C = 50 \text{mA}, I_B = 5 \text{mA}$	V _{CE(SAT)}			0.5	V
Base-Emitter saturation voltage	$I_C = 50 \text{mA}, I_B = 5 \text{mA}$	$V_{BE(SAT)}$			1	V
DC Commont Coin	$V_{CE} = 5V$, $I_C = 1mA$	h _{FE} 1	100			
DC Current Gain	$V_{CE}=5V$, $I_{C}=20mA$	h _{FE} 2	90		300	
Transition Frequency	V _{CE} = 10V, I _E =20mA	f⊤	50			MHz
Output Capacitance	V _{CB} =20V, f =1MHz	Cob			7	pF

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Notes:

- 1. Pulse test: $\leq 380\mu s$, duty cycle $\leq 2\%$
- 2. For DESIGN AID ONLY, not subject to production testing.

ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSC966CW RPG	SOT-223	2,500pcs / 13"Reel



Electrical Characteristics Curve

(Ta = 25°C, unless otherwise noted)

Figure 1. Static Characteristics

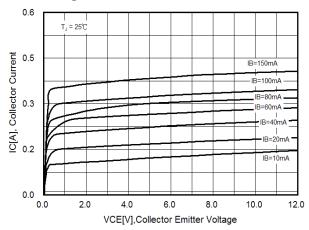


Figure 3. DC Current Gain

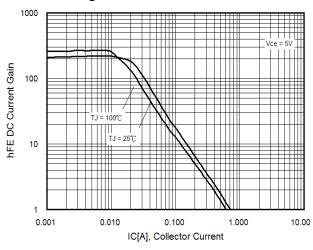


Figure 5. V_{BE(sat)} vs Ic

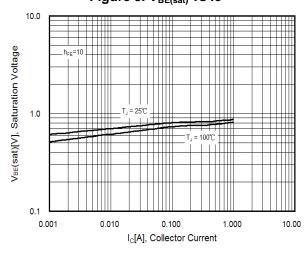


Figure 2. DC Current Gain

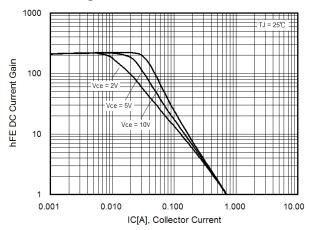


Figure 4. V_{CE(sat)} vs Ic

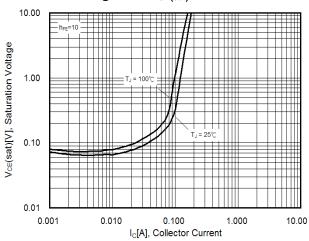
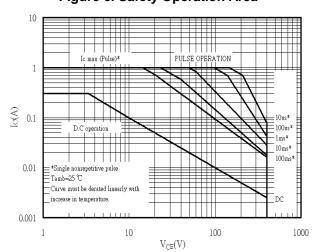


Figure 6. Safety Operation Area



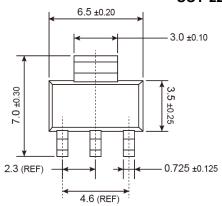
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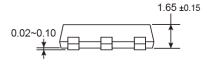
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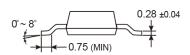


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

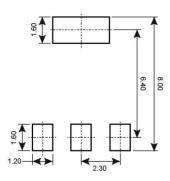
SOT-223







SUGGESTED PAD LAYOUT (Unit: Millimeters)



Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S = May T = Jun U = Jul V = Aug

W = Sep X = Oct Y = Nov Z = Dec

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L = Lot Code





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